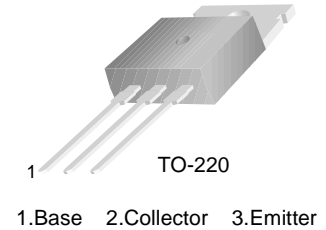


■ ■ APPLICATION: General Purpos Applications.

■ ■ MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CB0}	-30	V
Collector-emitter voltage	V_{CEO}	-30	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-3	A
Collector Power Dissipation	P_C	1.2~10	W
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	- 55~150	$^{\circ}\text{C}$


■ ■ ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h_{FE}	70		240		$V_{CE} = -2\text{V}$, $I_C = -500\text{mA}$
Collector Cut-off Current	I_{CBO}			-1.0	μA	$V_{CB} = -20\text{V}$, $I_E = 0$
Emitter Cut-off Current	I_{EBO}			-1.0	μA	$V_{EB} = -5\text{V}$, $I_C = 0$
Collector-Base Breakdown Voltage	BV_{CB0}	-30			V	$I_C = -1\text{mA}$, $I_E = 0$
Collector-Emitter Breakdown Voltage	BV_{CEO}	-30			V	$I_C = -10\text{mA}$, $I_B = 0$
Emitter-Base Breakdown Voltage	BV_{EBO}	-5			V	$I_E = -1\text{mA}$, $I_C = 0$
Base-Emitter Voltage	V_{BE}		-0.75	-1.0	V	$V_{CE} = -2\text{V}$, $I_C = -500\text{mA}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.3	-0.8	V	$I_C = -2\text{A}$, $I_B = -200\text{mA}$
Gain bandwidth product	f_T		100		MHz	$I_C = -500\text{mA}$, $V_{CE} = -2\text{V}$
Common Base Output Capacitance	C_{ob}		40		PF	$V_{CB} = -10\text{V}$, $I_E = 0$, $f = 1\text{MHz}$

■ ■ hFE Classification And Marking

Classification	O	Y
h_{FE}	70~140	120~240